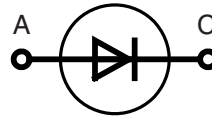
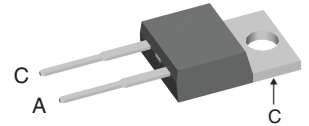


# Fast Recovery Epitaxial Diode (FRED)

$I_{FAV} = 11\text{ A}$   
 $V_{RRM} = 1200\text{ V}$   
 $t_{rr} = 50\text{ ns}$

$V_{RSM}$	$V_{RRM}$	Type
V	V	
1200	1200	DSEI 12-12A


**TO-220 AC**


A = Anode, C = Cathode

Symbol	Conditions	Maximum Ratings		
$I_{FRMS}$	$T_{VJ} = T_{VJM}$	25	A	
$I_{FAVM}$ ①	$T_C = 100^\circ\text{C}$ ; rectangular, $d = 0.5$	11	A	
$I_{FRM}$	$t_p < 10\ \mu\text{s}$ ; rep. rating, pulse width limited by $T_{VJM}$	150	A	
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ;	$t = 10\text{ ms}$ (50 Hz), sine	75	A
		$t = 8.3\text{ ms}$ (60 Hz), sine	80	
	$T_{VJ} = 150^\circ\text{C}$ ;	$t = 10\text{ ms}$ (50 Hz), sine	65	A
		$t = 8.3\text{ ms}$ (60 Hz), sine	70	
$I^2t$	$T_{VJ} = 45^\circ\text{C}$ ;	$t = 10\text{ ms}$ (50 Hz), sine	28	A <sup>2</sup> s
		$t = 8.3\text{ ms}$ (60 Hz), sine	27	
	$T_{VJ} = 150^\circ\text{C}$ ;	$t = 10\text{ ms}$ (50 Hz), sine	21	A <sup>2</sup> s
		$t = 8.3\text{ ms}$ (60 Hz), sine	20	
$T_{VJ}$		-40...+150	°C	
$T_{VJM}$		150	°C	
$T_{stg}$		-40...+150	°C	
$P_{tot}$	$T_C = 25^\circ\text{C}$	78	W	
$M_d$	mounting torque	0.4...0.6	Nm	
<b>Weight</b>	typical	2	g	

## Features

- International standard package JEDEC TO-220 AC
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low  $I_{RM}$ -values
- Soft recovery behaviour
- Epoxy meets UL 94V-0

## Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

## Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses
- Operating at lower temperature or space saving by reduced cooling

Symbol	Conditions	Characteristic Values		
		typ.	max.	
$I_R$	$V_R = V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$	250	$\mu\text{A}$
	$V_R = 0.8 \cdot V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$	150	$\mu\text{A}$
	$V_R = 0.8 \cdot V_{RRM}$	$T_{VJ} = 125^\circ\text{C}$	4	mA
$V_F$	$I_F = 12\text{ A}$	$T_{VJ} = 150^\circ\text{C}$	2.2	V
		$T_{VJ} = 25^\circ\text{C}$	2.6	V
$V_{T0}$	For power-loss calculations only		1.65	V
$r_T$	$T_{VJ} = T_{VJM}$		46.2	m $\Omega$
$R_{thJC}$		0.5	1.6	K/W
$R_{thCH}$			60	K/W
$R_{thJA}$				K/W
$t_{rr}$	$I_F = 1\text{ A}$ ; $-di/dt = 50\text{ A}/\mu\text{s}$ ; $V_R = 30\text{ V}$ ; $T_{VJ} = 25^\circ\text{C}$	50	70	ns
$I_{RM}$	$V_R = 540\text{ V}$ ; $I_F = 12\text{ A}$ ; $-di_F/dt = 100\text{ A}/\mu\text{s}$ $L \leq 0.05\ \mu\text{H}$ ; $T_{VJ} = 100^\circ\text{C}$	6.5	7.2	A

①  $I_{FAVM}$  rating includes reverse blocking losses at  $T_{VJM}$ .  $V_R = 0.8 \cdot V_{RRM}$ , duty cycle  $d = 0.5$   
Data according to IEC 60747

IXYS reserves the right to change limits, test conditions and dimensions.

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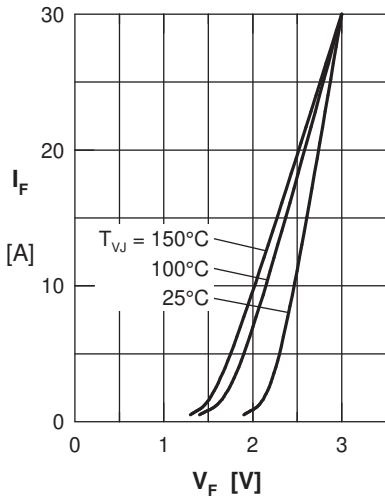


Fig. 1 Forward current  $I_F$  versus  $V_F$

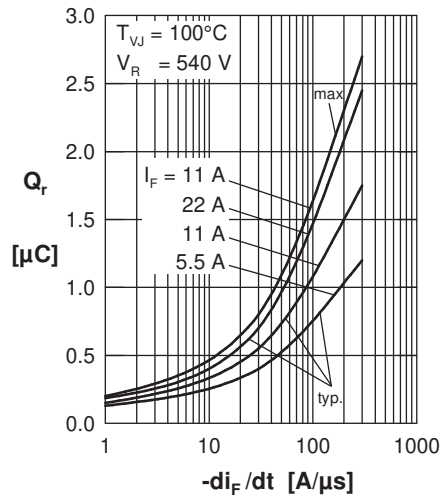


Fig. 2 Typ. reverse recov. charge  $Q_r$  versus  $-di_F/dt$

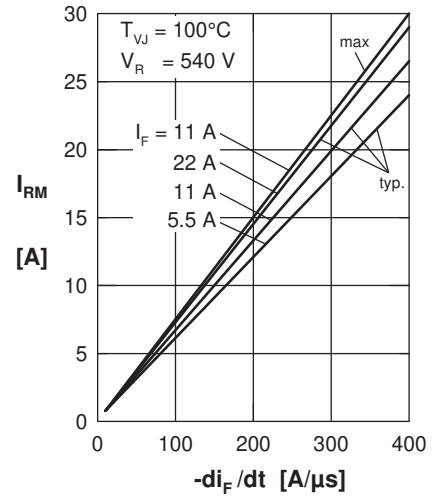


Fig. 3 Typ. peak reverse current  $I_{RM}$  versus  $-di_F/dt$

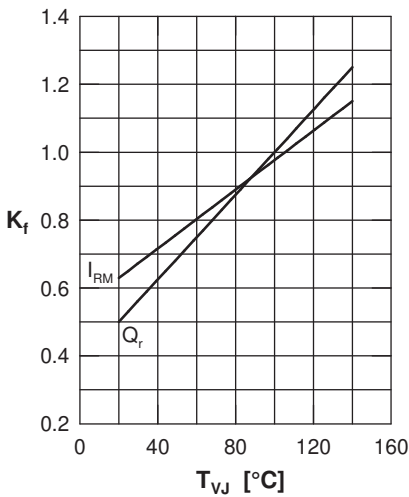


Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

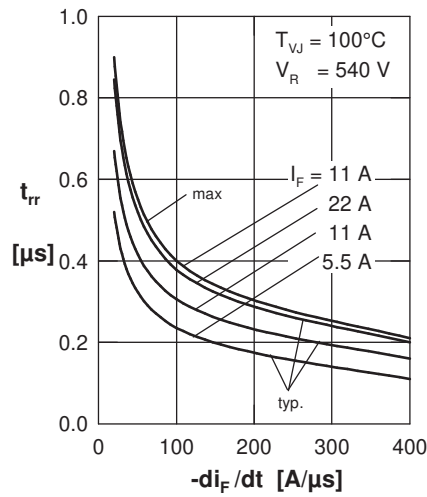


Fig. 5 Typ. recovery time  $t_{tr}$  versus  $-di_F/dt$

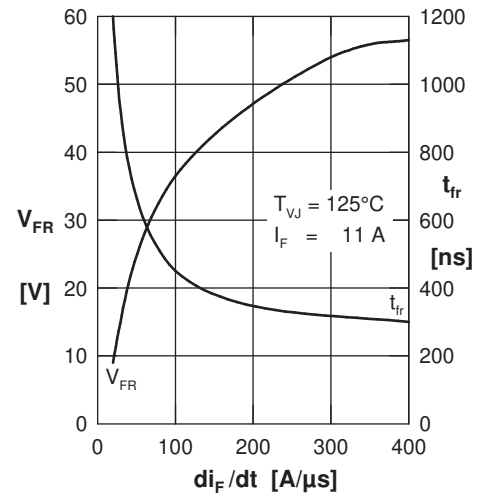


Fig. 6 Typ. peak forward voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_F/dt$

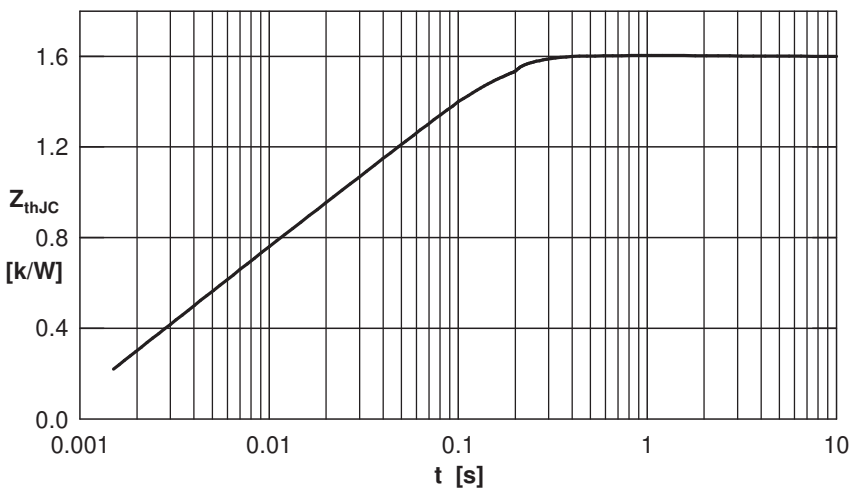
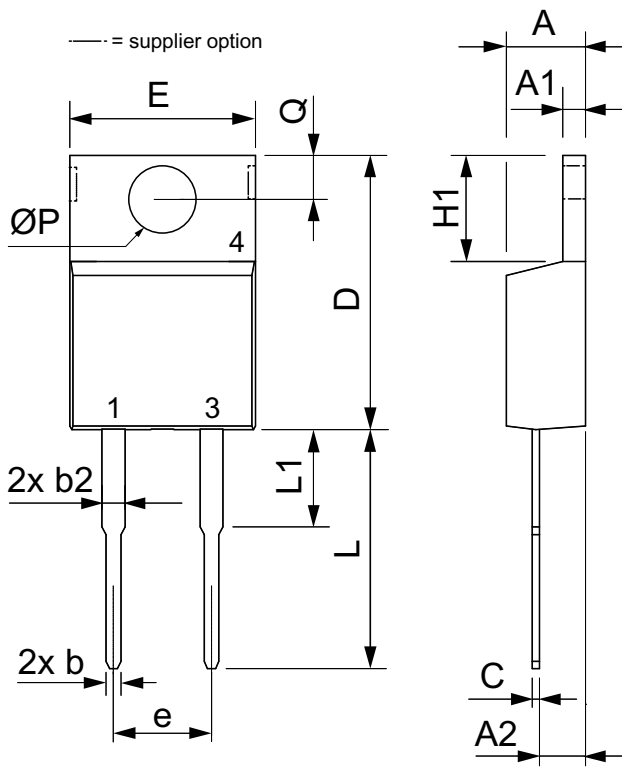


Fig. 7 Transient thermal impedance junction to case

## Dimensions TO-220 AC



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125